Product data sheet

1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220 plastic package.





2. Features and benefits

- · Trench structure
- High junction temperature up to 150°C
- · Low forward voltage drop, negligible switching losses
- High efficiency

3. Applications

- · DC to DC converters
- · Freewheeling diode
- · OR-ing diode
- · Switched mode power supply rectifier

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values		Unit				
Absolute maximum rating										
V_{RRM}	repetitive peak reverse voltage			120			V			
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 120 °C; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		20			А			
I _{O(AV)}	average output current	δ = 0.5 ; square-wave pulse; $T_{mb} \le$ 120 °C; both diodes conducting		40			А			
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit			
Static ch	aracteristics									
V _F	forward voltage	$I_F = 20 \text{ A}$; $T_j = 25 ^{\circ}\text{C}$; per diode; Fig. 6		- 0.95 1.05		V				
I _R	reverse current	V_R = 120 V; T_j = 25 °C; per diode; Fig. 7; Fig. 8		- 4 20		μА				

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode		A1 A2
3	A2	anode 2		K sym125
mb	К	mounting base; connected to cathode		cymr2c

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WN3S40120C	TO220	WN3S40120CQ	Tube	50	SOT78	13-Jun-2008

7. Marking

Table 4. Marking codes

Type number	Marking codes
WN3S40120C	WN3S40 120C

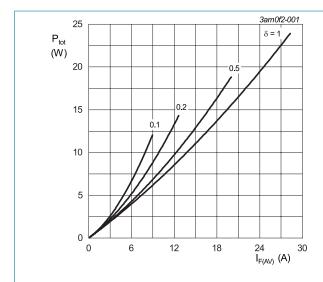
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

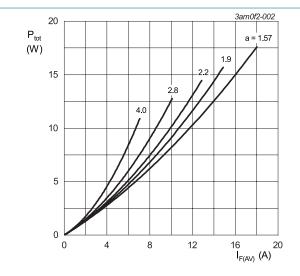
Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			120	V
V_{RWM}	crest working reverse voltage			120	V
V_R	reverse voltage	DC		120	V
$I_{F(AV)}$	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 120$ °C; per diode; Fig. 1; Fig. 2; Fig. 3		20	А
$I_{O(AV)}$	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 120$ °C; both diodes conducting		40	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		250	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		275	А
T _{stg}	storage temperature			-40 to 150	°C
T _j	junction temperature		[1]	-40 to 150	°C

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient: $dP_{tot}/dT_j < 1/R_{th(j-a)}$



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_0 = 0.614 \text{ V}; R_s = 0.0082 \Omega$ Forward newer dissipation

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor = $I_{F(RMS)}$ / $I_{F(AV)}$ V_o = 0.614 V; R_s = 0.0082 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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Dual power Schottky diode

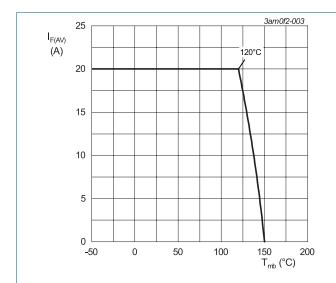


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

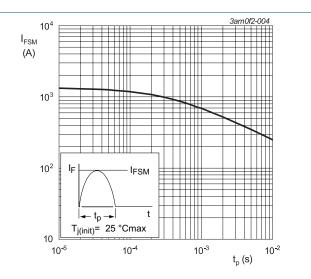


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance		per diode; <u>Fig. 5</u>		-	-	1.6	K/W
	from junction to mounting base	both diodes conducting		-	-	8.0	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		-	60	-	K/W

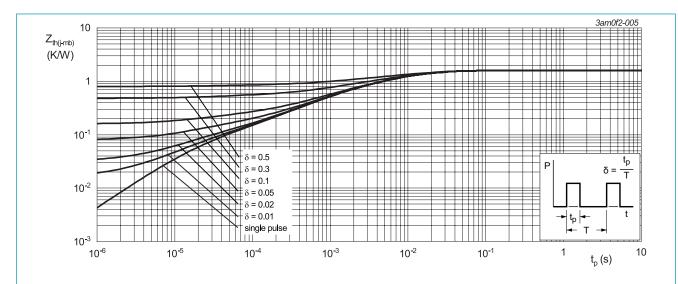
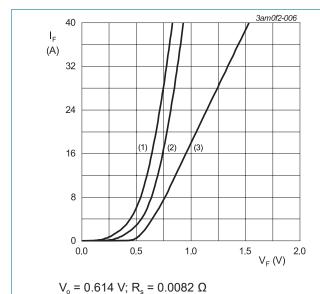


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

10. Characteristics

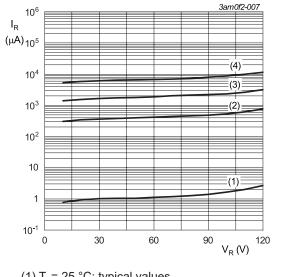
Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V_{F}	forward voltage	I _F = 20 A; T _j = 25 °C; per diode; <u>Fig. 6</u>		-	0.95	1.05	V
		I _F = 20 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	0.72	-	V
				I _F = 15 A; T _j = 25 °C; per diode; <u>Fig. 6</u>		-	0.82
		I _F = 15 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	0.66	-	V
		I _F = 2 A; T _j = 25 °C; per diode; <u>Fig. 6</u>		-	0.47	-	V
		I _F = 2 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	0.39	-	V
I _R reverse current		V _R = 120 V; T _j = 25 °C; per diode; Fig. 7; Fig. 8		-	4	20	μA
		V _R = 120 V; T _j = 125 °C; per diode; Fig. 7; Fig. 8		-	3	20	mA



(1) T_i = 150 °C; typical values (2) $T_j = 150$ °C; maximum values (3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



(1) T_i = 25 °C; typical values

(2) T_i = 100 °C; typical values

(3) T_j = 125 °C; typical values

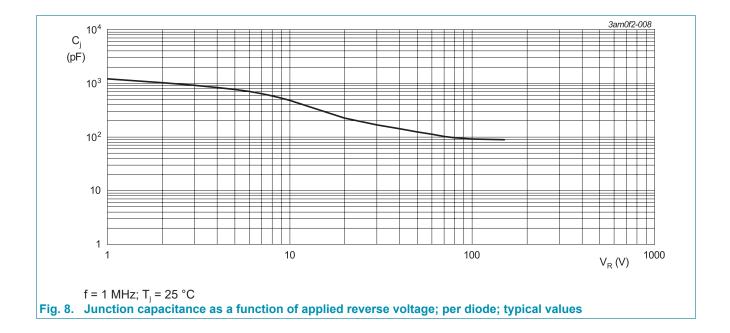
(4) T_i = 150 °C; typical values

Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

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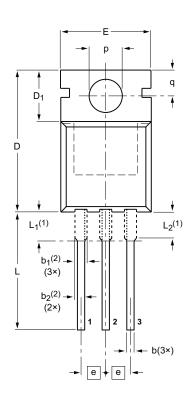
WN3S40120C

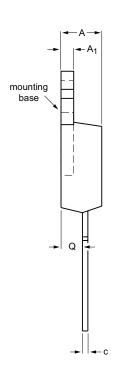
Dual power Schottky diode



11. Package outline







0 5 10 mm scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE			REFER	ENCES	EUROPEAN	ISSUE DATE
'	VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
	SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Product data sheet

WeEn Semiconductors WN3S40120C

Dual power Schottky diode

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